

To: Facsimile Number: 703-872-9306

Total Pages Sent 10

From:

Texas Instruments Incorporated
Facsimile: 972-917-4418

RECEIVED
CENTRAL FAX CENTER

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

FEB 07 2005

In re the Application of

Applicant Yuanning Chen, et al. Docket Number: TI-35022.1

Serial No.: 10/719,280 Art Unit: 2813

Filed: 11/21/03 Examiner: Jack S. J. Chen

For: Use of Hafnium Silicon Oxynitride as the Cap Layer of the Sidewall Spacer

CERTIFICATION OF FACSIMILE TRANSMISSION

I hereby certify that the following papers are being transmitted by facsimile to the U.S. Patent and Trademark Office on the date shown below:

Karen Vertz
Karen Vertz

2-7-05
Date

FACSIMILE COVER SHEET

<input checked="" type="checkbox"/> FACSIMILE COVER SHEET	<input checked="" type="checkbox"/> AMENDMENT <u>116 (8 Pages)</u>
<input checked="" type="checkbox"/> NEW APPLICATION	<input checked="" type="checkbox"/> EOT <u>1 month</u>
<input checked="" type="checkbox"/> DECLARATION	<input checked="" type="checkbox"/> NOTICE OF APPEAL
<input checked="" type="checkbox"/> ASSIGNMENT	<input checked="" type="checkbox"/> APPEAL <u>(# Pages)</u>
<input checked="" type="checkbox"/> FORMAL DRAWINGS	<input checked="" type="checkbox"/> ISSUE FEE & PUBLICATION FEE <u>(1 Page)</u>
<input checked="" type="checkbox"/> INFORMAL DRAWINGS	<input checked="" type="checkbox"/> REPLY BRIEF (IN TRIPPLICATE) <u>(# Pages)</u>
<input checked="" type="checkbox"/> CONTINUATION APP'N	<input checked="" type="checkbox"/> ELECTION
<input checked="" type="checkbox"/> DIVISIONAL APP'N	
NAME OF INVENTOR(S): Yuanning Chen, et al.	
RECEIPT DATE & SERIAL NO.: Serial No.: 10/719,280 Filing Date: 11/21/03	
TITLE OF INVENTION: Use of Hafnium Silicon Oxynitride as the Cap Layer of the Sidewall Spacer	
TI FILE NO.: TI-35022.1	DEPOSIT ACCT. NO.: 20-0668
FAXED: 2-7-05 DUE: 12-18-04 ATTY/SECY: RAK/kjv	

This facsimile is intended only for the use of the address named and contains legally privileged and/or confidential information. If you are not the intended recipient of this telecopy, you are hereby notified that any dissemination, distribution, copying or use of this communication is strictly prohibited. Applicable privileges are not waived by virtue of the document having been transmitted by Facsimile. Any misdirected facsimiles should be returned to the sender by mail at the address indicated on this cover sheet.

Texas Instruments Incorporated
PO Box 655474, MS 3998
Dallas, TX 75265-5474

RECEIVED
CENTRAL FAX CENTER

FEB 07 2005

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: Chen et al.

Docket No.: TI-35022.1

Serial No.: 10/719,280

Art Unit: 2813

Filed: 11/21/03

Examiner: Chen, Jack S J

Title: Use Of Hafnium Silicon Oxynitride As The Cap Layer Of The Sidewall
Spacer

AMENDMENT UNDER 37 C.F.R. §1.116

February 7, 2005

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Commissioner:

CERTIFICATION OF FACSIMILE TRANSMISSION
I hereby certify that the above correspondence is being transmitted by facsimile to the U.S. Patent and Trademark Office at 703-872-9306 on the date shown below.

Karen Vertz
Karen Vertz

2-7-05
Date

In response to the Office Action, dated 10/18/2004, in the above-identified patent application, please make the following amendments. They are respectfully submitted as a full and complete response to that Action. Charge any required fees to the deposit account of Texas Instruments Incorporated, Account No. 20-0668.